



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Application of: **WATANABE, et al.**

Serial No.: 09/320,271

Filed: May 27, 1999

Group Art Unit: 2825

Examiner: Calvin Lee

P.T.O. Confirmation No.: 4409

FOR: **SEMICONDUCTOR DEVICE AND FABRICATION METHOD THEREOF**

AMENDMENT UNDER 37 CFR §1.111

Commissioner for Patents
Washington, D.C. 20231

July 9, 2002

Sir:

In response to the Office Action dated **April 9, 2002**, please amend the above identified application as follows:

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IN THE CLAIMS:

Please amend claim 1 as follows:

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1. **(Four Times Amended)** A fabrication method of a semiconductor device comprising the steps of:
forming a first insulation layer on a flat underlying face over a substrate,
introducing impurities into said first insulation layer, and
embedding and forming a first conductive layer in said first insulation layer.